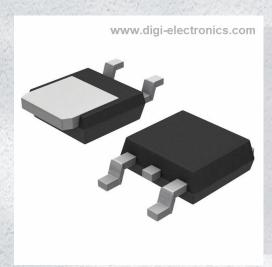


# MJD3055T4G Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MJD3055T4G-DG

Manufacturer onsemi

Manufacturer Product Number MJD3055T4G

Description TRANS NPN 60V 10A DPAK

Detailed Description Bipolar (BJT) Transistor NPN 60 V 10 A 2MHz 1.75 W

Surface Mount DPAK



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
MJD3055T4G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	10 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
60 V	8V @ 3.3A, 10A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
50μΑ	20 @ 4A, 4V
Power - Max:	Frequency - Transition:
1.75 W	2MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-252-3, DPAK (2 Leads + Tab), SC-63	DPAK
Base Product Number:	
MJD3055	

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

# **Complementary Power Transistors**

# **DPAK for Surface Mount Applications**

Designed for general purpose amplifier and low speed switching applications.

#### **Features**

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to MJE2955 and MJE3055
- High Current Gain-Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	60	Vdc
Collector-Base Voltage	V <sub>CB</sub>	70	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5	Vdc
Collector Current	I <sub>C</sub>	10	Adc
Base Current	I <sub>B</sub>	6	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub> <sup>†</sup>	20 0.16	W W/°C
Total Power Dissipation (Note 1)  @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
ESD - Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

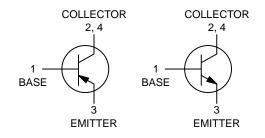


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# SILICON POWER TRANSISTORS 10 AMPERES 60 VOLTS, 20 WATTS

#### COMPLEMENTARY





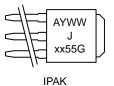


DPAK CASE 369C STYLE 1

IPAK CASE 369D STYLE 1

#### **MARKING DIAGRAMS**





DPAK

A = Assembly Location

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

<sup>†</sup>Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

<sup>2.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	-		•	*
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	60	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	50	μAdc
Collector Cutoff Current $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 150^{\circ}\text{C})$	I <sub>CEX</sub>	- -	0.02 2	mAdc
Collector Cutoff Current $(V_{CB} = 70 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 70 \text{ Vdc}, I_E = 0, T_C = 150^{\circ}\text{C})$	Ісво	- -	0.02 2	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	0.5	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) ( $I_C = 4$ Adc, $V_{CE} = 4$ Vdc) ( $I_C = 10$ Adc, $V_{CE} = 4$ Vdc)	h <sub>FE</sub>	20 5	100	_
Collector–Emitter Saturation Voltage (Note 3) $(I_C = 4 \text{ Adc}, I_B = 0.4 \text{ Adc})$ $(I_C = 10 \text{ Adc}, I_B = 3.3 \text{ Adc})$	V <sub>CE(sat)</sub>	- -	1.1 8	Vdc
Base–Emitter On Voltage (Note 3) (I <sub>C</sub> = 4 Adc, V <sub>CE</sub> = 4 Vdc)	V <sub>BE(on)</sub>	-	1.8	Vdc
DYNAMIC CHARACTERISTICS			•	•
Current–Gain – Bandwidth Product (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f = 500 kHz)	f <sub>T</sub>	2	_	MHz
Pulsa Tast: Pulsa Width < 300 us Duty Cycla < 2%	•		•	+

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

#### **TYPICAL CHARACTERISTICS**

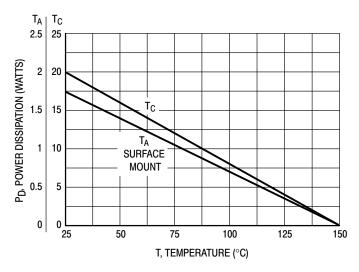


Figure 1. Power Derating

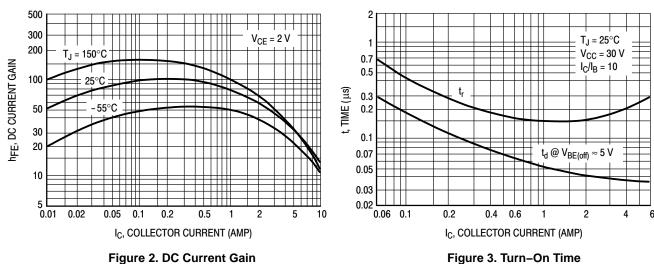


Figure 2. DC Current Gain

1.4

1.2

8.0

0.6

0.4

0.2

0

0.1

V, VOLTAGE (VOLTS)

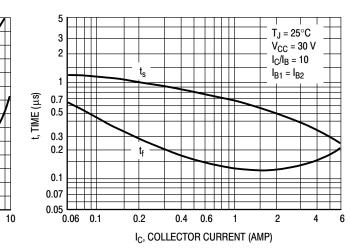
 $T_J = 25^{\circ}C$ 

 $V_{BE(sat)} @ I_C/I_B = 10$ 

 $V_{BE}$  @  $V_{CE}$  = 2 V

 $V_{CE(sat)} @ I_C/I_B = 10$ 

0.2 0.3



I<sub>C</sub>, COLLECTOR CURRENT (AMP) Figure 4. "On" Voltages, MJD3055

Figure 5. Turn-Off Time

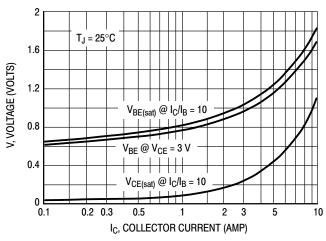
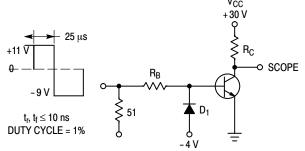


Figure 6. "On" Voltages, MJD2955



 $R_B$  and  $R_C$  varied to obtain desired current levels  $D_1 \ \text{MUST BE FAST RECOVERY TYPE, eg:} \\ 1N5825 \ \text{USED ABOVE I}_B \approx 100 \ \text{mA} \\ \text{MSD6100 USED BELOW I}_B \approx 100 \ \text{mA}$ 

Figure 7. Switching Time Test Circuit

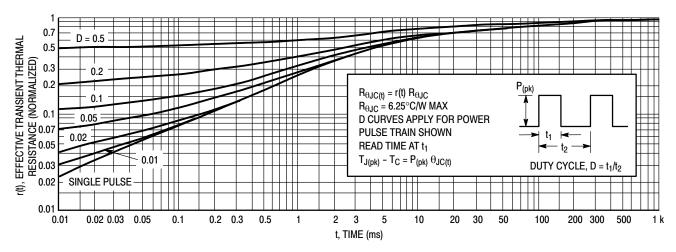


Figure 8. Thermal Response

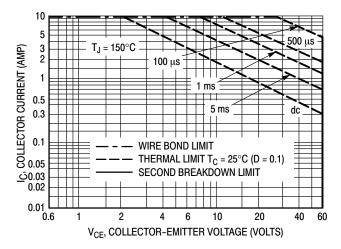


Figure 9. Maximum Forward Bias Safe Operating Area

#### Forward Bias Safe Operating Area Information

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on  $T_{J(pk)} = 150^{\circ} C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ} C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

#### **ORDERING INFORMATION**

Device	Package Type	Package	Shipping <sup>†</sup>
MJD2955G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD2955-1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD2955T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD2955T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD3055G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD3055T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD3055T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable



# **MECHANICAL CASE OUTLINE**

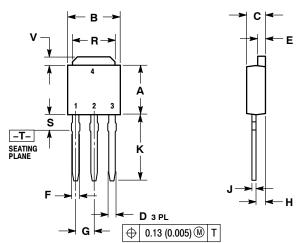
**PACKAGE DIMENSIONS** 

#### **DPAK INSERTION MOUNT**

CASE 369 ISSUE O

**DATE 02 JAN 2000** 





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090	BSC	2.29	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1 27

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		STYLE 5:		STYLE 6:	
PIN 1.	BASE	PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	GATE	PIN 1.	MT1
2.	COLLECTOR	2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE	2.	MT2
3.	EMITTER	3.	SOURCE	3.	ANODE	3.	GATE	3.	CATHODE	3.	GATE
4.	COLLECTOR	4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE	4.	MT2

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DESCRIPTION:	DPAK INSERTION MOUNT		PAGE 1 OF 1	

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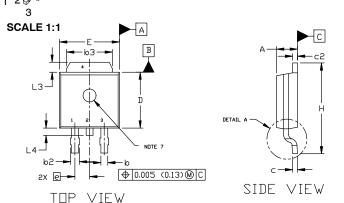


# **MECHANICAL CASE OUTLINE**

# PACKAGE DIMENSIONS

#### **DPAK (SINGLE GAUGE)** CASE 369C **ISSUE G**

**DATE 31 MAY 2023** 



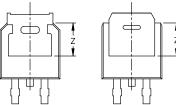


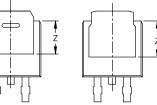
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63, L3. AND Z. L3, AND Z.

  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
  PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
  GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
  DIMENSIONS D AND E ARE DETERMINED AT THE
  OUTERMOST EXTREMES OF THE PLASTIC BODY.
  DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
  DETININAL MOLD ESCALUPE.

- OPTIONAL MOLD FEATURE.

DIM	INC	HES	MILLIM	ETERS
ויונע	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
C	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
Ε	0.250	0.265	6.35	6.73
е	0.090	BSC	2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	





BOTTOM VIEW

2.58

[0.102]

1.60

[0.063]

5.80

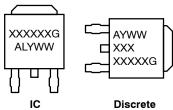
6.17 [0.243] RECOMMENDED MOUNTING FOOTPRINT\*

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

BOTTOM VIEW AL TERNATE CONSTRUCTIONS

[0.228] 6.20 -L2 GAUGE PLANE [0.244] С Δ1 3.00 [0.118] DETAIL Δ CW ROTATED 90°

# **GENERIC MARKING DIAGRAM\***



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

STYLE 1: PIN 1. BASE STYLE 2: PIN 1. GATE STYLE 3: PIN 1. ANODE STYLE 4: PIN 1. CATHODE STYLE 5: PIN 1. GATE 2. COLLECTOR 2. DRAIN 2. CATHODE 2. ANODE 2. ANODE 3 SOURCE 3 CATHODE 3 FMITTER 3 ANODE 3 GATE COLLECTOR 4. DRAIN CATHODE 4. ANODE ANODE

STYLE 6: STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 8: STYLE 9: STYLE 10: PIN 1. MT1 2. MT2 PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE PIN 1. CATHODE 2. ANODE 3 CATHODE 3 FMITTER 3 RESISTOR ADJUST 3 GATE 4. COLLECTOR 4. CATHODE 4. ANODE CATHODE

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1	

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